C Thomidis

List of Publications by Year in descending order

14	262	840776 11	1125743 13
papers	citations	h-index	g-index

14	14	14	404
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Phosphorous Diffusion in N2+-Implanted Germanium during Flash Lamp Annealing: Influence of Nitrogen on Ge Substrate Damage and Capping Layer Engineering. ECS Journal of Solid State Science and Technology, 2017, 6, P418-P428.	1.8	5
2	Strong Diffusion Suppression of Low Energy-Implanted Phosphorous in Germanium by N2 Co-Implantation. ECS Solid State Letters, 2015, 4, P47-P50.	1.4	11
3	Molecular beam epitaxy growth of AlGaN quantum wells on 6H-SiC substrates with high internal quantum efficiency. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, 02B119.	1.2	22
4	InGaN-based LEDs grown by plasma-assisted MBE on (0001) sapphire with GaN QDs in the nucleation layer. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2309-2311.	0.8	7
5	Growth and properties of nearâ€UV light emitting diodes based on InN/GaN quantum wells. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 1070-1073.	1.8	57
6	Growth of IIIâ€nitride quantum dots and their applications to blueâ€green LEDs. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 2560-2565.	1.8	28
7	InGaN-based LEDs grown by plasma-assisted MBE on (0001) sapphire with GaN QDs in the nucleation layer. , 2008, 5, 2309.		1
8	Growth of InN films by RF plasma-assisted MBE and cluster beam epitaxy. Journal of Crystal Growth, 2006, 288, 254-260.	1.5	15
9	High power ultraviolet light emitting diodes based on GaNâˆ•AlGaN quantum wells produced by molecular beam epitaxy. Journal of Applied Physics, 2006, 100, 104506.	2.5	21
10	Enhanced internal quantum efficiency and light extraction efficiency from textured GaNâˆ•AlGaN quantum wells grown by molecular beam epitaxy. Journal of Applied Physics, 2006, 99, 064904.	2.5	22
11	Growth and silicon doping of AlGaN films in the entire alloy composition by molecular beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2220-2223.	0.8	18
12	Ultraviolet electroabsorption modulator based on AlGaNâˆ•GaN multiple quantum wells. Journal of Applied Physics, 2005, 97, 123515.	2.5	22
13	Well width dependence of disorder effects on the optical properties of AlGaNâˆ•GaN quantum wells. Applied Physics Letters, 2004, 85, 3068-3070.	3.3	13
14	Investigation of excitons in AlGaN/GaN multiple quantum wells by lateral photocurrent and photoluminescence spectroscopies. Journal of Applied Physics, 2004, 95, 3495-3502.	2.5	20